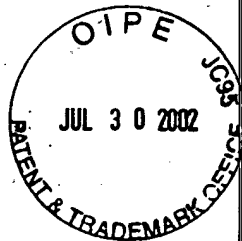


IN THE UNITED STATES PATENT AND TRADEMARK OFFICE



Applicant(s): Timothy K. Carns, Lee J. DeBruler, John L. Horvath, Michael J. Westphal  
Assignee: ZiLOG, Inc.  
Title: PROCESS TO IMPROVE HIGH PERFORMANCE CAPACITOR PROPERTIES IN INTEGRATED MOS TECHNOLOGIES  
Serial No.: 09/351,544 Filing Date: July 12, 1999  
Examiner: Brock II, P. Group-Art Unit: 2815  
Docket No.: M-10889 US (Formerly ZILG.204US0)

San Francisco, California  
August 30, 2002

BOX RCE  
COMMISSIONER FOR PATENTS  
Washington, D. C. 20231

AMENDMENT

Dear Sir:

Responsive to the Official Action mailed on May 3, 2002, applicant responds to the Official Action as follows:

In the Claims:

Please cancel, without prejudice, claims 1, 2, 12-14, and 31-35.

Please replace claim 3 with the following (a marked up version is in the Appendix):

--3.(Twice Amended) A method of forming a capacitor in an integrated circuit comprising:  
forming a bottom electrode layer on a semiconductor body;  
forming a dielectric layer over at least a portion said bottom electrode;  
forming a top electrode layer over at least a portion of said dielectric layer;  
removing a portion of said top electrode layer to expose a portion of the dielectric layer;  
subsequently removing at least a portion of said exposed portion of the dielectric layer to expose a portion of said lower electrode layer;

LAW OFFICES OF  
SKJERNEN MORRILL LLP  
Three Embarcadero Center  
28<sup>th</sup> Floor  
SAN FRANCISCO, CA 94111  
(415) 217-6000  
FAX (415) 434-0646